

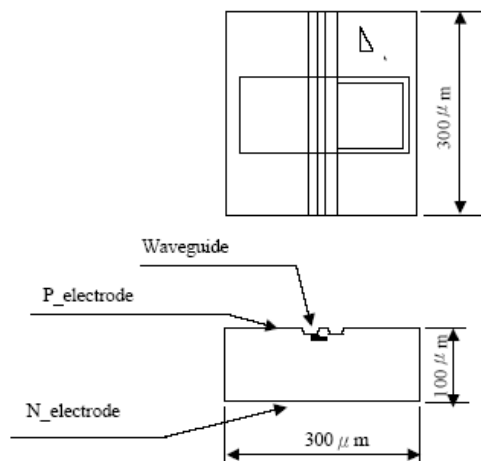


CHIP-1310-P5

■ Specifications

- (1) Size : 300*300*100 μm
- (2) Device: Laser diode bare chip
- (3) Structure: Double channel , single ridge waveguide

■ External dimensions(Unit : μm)



Bonding pad locate on the right side to the emitting direction.

Maximum Ratings ($T_c = 25^{\circ}\text{C}$)

Characteristic	Symbol	Rating	Unit
Optical Output Power	Po	7	mW
LD Reverse Voltage	Vr (LD)	2	V
Operation Temperature	Top	-40 ~ +85	$^{\circ}\text{C}$
Storage Temperature	Tstg	-40 ~ +125	$^{\circ}\text{C}$



Optical-electrical characteristics ($T_c = 25^{\circ}\text{C}$)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Threshold Current	I_{th}	$T_c = 25^{\circ}\text{C}$	-	10	15	mA
Operating Current	I_{op}	$T_c = -40 \sim +85^{\circ}\text{C}$	-	22	35	mA
Operation Voltage	V_{op}	$P_o = 5\text{mW}$	-	1.3	1.5	V
Slope Efficiency	SE	$P_o = 1 \text{ to } 4\text{mW}$	0.25	0.35	-	mW/mA
Lasing Wavelength	λ	$P_o = 5\text{mW}$	1290	1310	1330	nm
Spectral Width	$\Delta\lambda$	$P_o = 5\text{mW}$	-	3	5	nm
Optical Output Power	P_o	CW, Kink free	5	-	-	mW
P-I Kink	K_i	$P_o < 5\text{mW}$	-	-	20	%
Beam Divergence (FWHM)	Parallel	$\theta //$	-	18	-	deg.
	Perpendicular	$\theta \perp$	-	38	-	deg.